New Jersey Semi-Conductor Products, Inc.

20 STERN AVE.
SPRINGFIELD, NEW JERSEY 07081
U.S.A.

TELEPHONE: (973) 376-2922
(212) 227-6005
FAX: (973) 376-8960

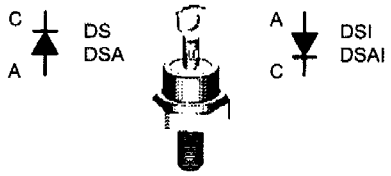
Rectifier Diode
Avalanche Diode

V_{RRM} = 800-1800 V
$I_{F(RMS)}$ = 40 A
$I_{F(AV)M}$ = 25 A

V_{RSM} V	$V_{(BR)min}$ ① V	V_{RRM} V	Anode on stud	Cathode on stud
900	-	800	DS 17-08A	DSI 17-08A
1300	-	1200	DS 17-12A	DSI 17-12A
1300	1300	1200	DSA 17-12A	DSAI 17-12A
1700	1750	1600	DSA 17-16A	DSAI 17-16A
1900	1950	1800	DSA 17-18A	DSAI 17-18A

① Only for Avalanche Diodes

DO-203 AA



A = Anode C = Cathode

Symbol	Test Conditions		Maximum Ratings	
$I_{F(RMS)}$	$T_{VJ} = T_{VJM}$		40	A
$I_{F(AV)M}$	T_{case} = 125°C; 180° sine		25	A
P_{RSM}	DSA(I) types, $T_{VJ} = T_{VJM}$, t_p = 10 µs		7	kW
I_{FSM}	T_{VJ} = 45°C;	t = 10 ms (50 Hz), sine	370	A
	V_R = 0	t = 8.3 ms (60 Hz), sine	400	A
	$T_{VJ} = T_{VJM}$	t = 10 ms (50 Hz), sine	300	A
	V_R = 0	t = 8.3 ms (60 Hz), sine	320	A
I^2t	T_{VJ} = 45°C	t = 10 ms (50 Hz), sine	680	A^2s
	V_R = 0	t = 8.3 ms (60 Hz), sine	660	A^2s
	$T_{VJ} = T_{VJM}$	t = 10 ms (50 Hz), sine	450	A^2s
	V_R = 0	t = 8.3 ms (60 Hz), sine	430	A^2s
T_{VJ}			-40...+180	°C
T_{VJM}			180	°C
T_{stg}			-40...+180	°C
M_d	Mounting torque		2.2-2.8	Nm
			19-25	lb.in.
Weight			6	g

Symbol	Test Conditions	Characteristic Values		
I_R	$T_{VJ} = T_{VJM}$; $V_R = V_{RRM}$	≤	4	mA
V_F	I_F = 55 A; T_{VJ} = 25°C	≤	1.36	V
V_{T0}	For power-loss calculations only		0.85	V
r_T	$T_{VJ} = T_{VJM}$		8	mΩ
R_{thJC}	DC current		1.5	K/W
R_{thJH}	DC current		2.1	K/W
d_S	Creepage distance on surface		2.05	mm
d_A	Strike distance through air		2.05	mm
a	Max. allowable acceleration		100	m/s^2

Features
- International standard package, JEDEC DO-203 AA (DO-4)
- Planar glassivated chips

Applications
- Supplies for DC power equipment
- DC supply for PWM inverter
- Field supply for DC motors
- Battery DC power supplies

Advantages
- Space and weight savings
- Simple mounting
- Improved temperature and power cycling
- Reduced protection circuits

Dimensions in mm (1 mm = 0.0394")